MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3, NSBA114YF3

Digital Transistors (BRT) R1 = 10 kΩ, R2 = 47 kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base−emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector−Base Voltage	V_{CBO}	50	Vdc
Collector−Emitter Voltage	V_{CEO}	50	Vdc
Collector Current − Continuous	I_C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	$V_{IN(rev)}$	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ON Semiconductor®

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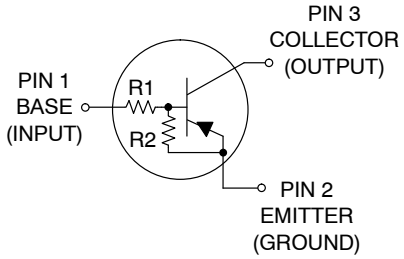
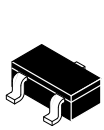
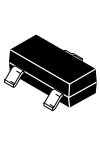
PIN CONNECTIONS



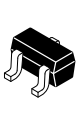
MARKING DIAGRAMS



SC−59
CASE 318D
STYLE 1



SOT−23
CASE 318
STYLE 6



SC−70/SOT−323
CASE 419
STYLE 3

SC−75
CASE 463
STYLE 1

SOT−723
CASE 631AA
STYLE 1

SOT−1123
CASE 524AA
STYLE 1

XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending up- on manufacturing location.

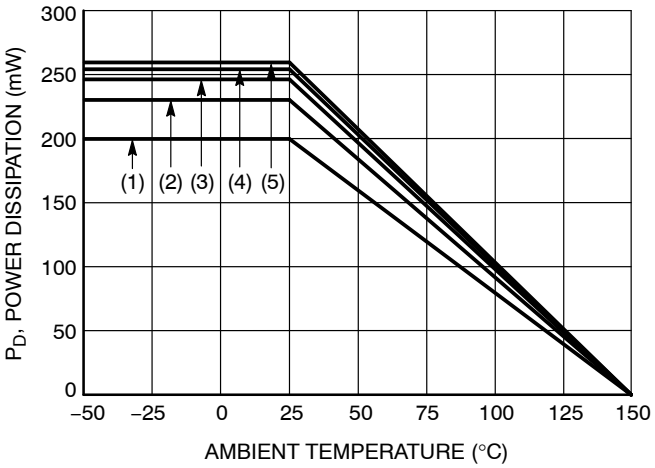
ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2114T1G, SMUN2114T1G*	6D	SC−59	3,000 / Tape & Reel
MMUN2114LT1G, SMMUN2114LT1G*	A6D	SOT−23	3,000 / Tape & Reel
MMUN2114LT3G, NSVMMUN2114LT3G*	A6D	SOT−23	10,000 / Tape & Reel
MUN5114T1G, SMUN5114T1G*	6D	SC−70/SOT−323	3,000 / Tape & Reel
SMUN5114T3G	6D	SC−70/SOT−323	10,000 / Tape & Reel
DTA114YET1G, SDTA114YET1G*	6D	SC−75	3,000 / Tape & Reel
DTA114YM3T5G, NSVDTA114YM3T5G*	6D	SOT−723	8,000 / Tape & Reel
NSBA114YF3T5G	K	SOT−1123	8,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



(1) SC−75 and SC−70/SOT−323; Minimum Pad
(2) SC−59; Minimum Pad
(3) SOT−23; Minimum Pad
(4) SOT−1123; 100 mm^2, 1 oz. copper trace
(5) SOT−723; Minimum Pad

Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC−59) (MUN2114)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 230 338 1.8 2.7	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	264 287	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−23) (MMUN2114L)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 246 400 2.0 3.2	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−70/SOT−323) (MUN5114)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 202 310 1.6 2.5	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	280 332	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−75) (DTA114YE)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 200 300 1.6 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−723) (DTA114YM3)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 1) (Note 2) (Note 1) (Note 2)	P_D	 260 600 2.0 4.8	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	480 205	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT−1123) (NSBA114YF3)				
Total Device Dissipation T_A = 25°C Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P_D	 254 297 2.0 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 x 1.0 Inch Pad.
3. FR−4 @ 100 mm^2, 1 oz. copper traces, still air.
4. FR−4 @ 500 mm^2, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	–	–	100	nAdc
Collector−Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I_{CEO}	–	–	500	nAdc
Emitter−Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I_{EBO}	–	–	0.2	mAdc
Collector−Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector−Emitter Breakdown Voltage (Note 5) (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I_C = 5.0 mA, V_{CE} = 10 V)	h_{FE}	80	140	–	
Collector − Emitter Saturation Voltage (Note 5) (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) (V_{CE} = 5.0 V, I_C = 100 μA)	$V_{i(off)}$	–	0.7	0.5	Vdc
Input Voltage (on) (V_{CE} = 0.2 V, I_C = 1.0 mA)	$V_{i(on)}$	1.4	0.9	–	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R_1/R_2	0.17	0.21	0.25	

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS
MUN2114, MMUN2114L, MUN5114, DTA114YE, DTA114YM3

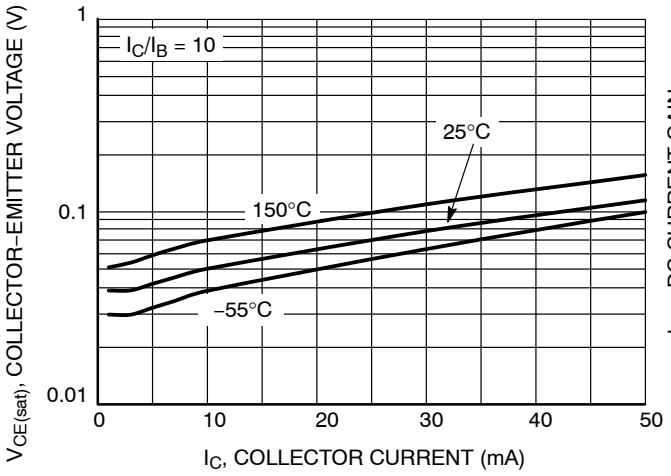


Figure 2. $V_{CE(sat)}$ vs. I_C

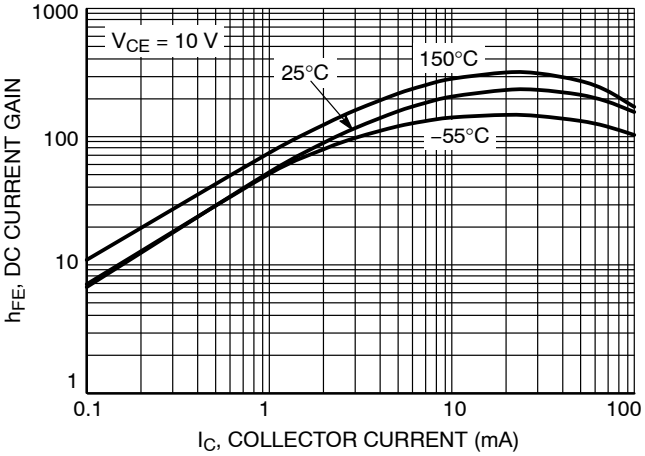


Figure 3. DC Current Gain

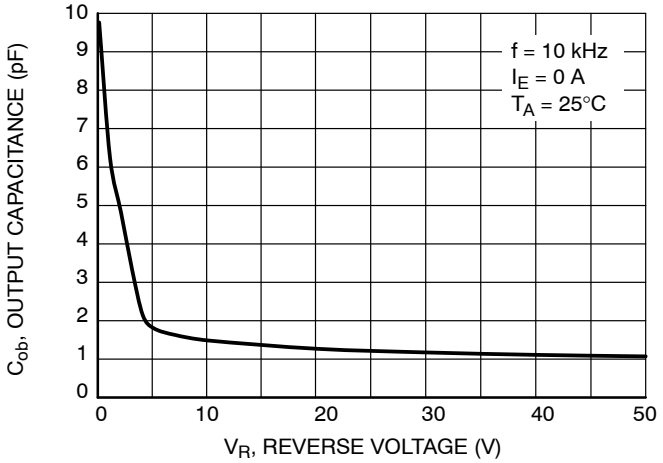


Figure 4. Output Capacitance

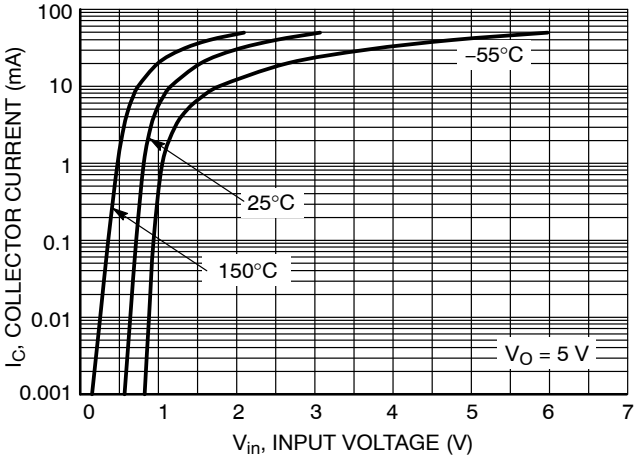


Figure 5. Output Current vs. Input Voltage

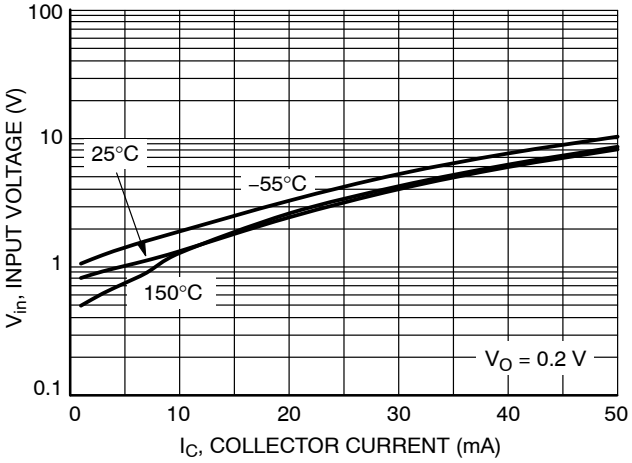


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS
NSBA114YF3

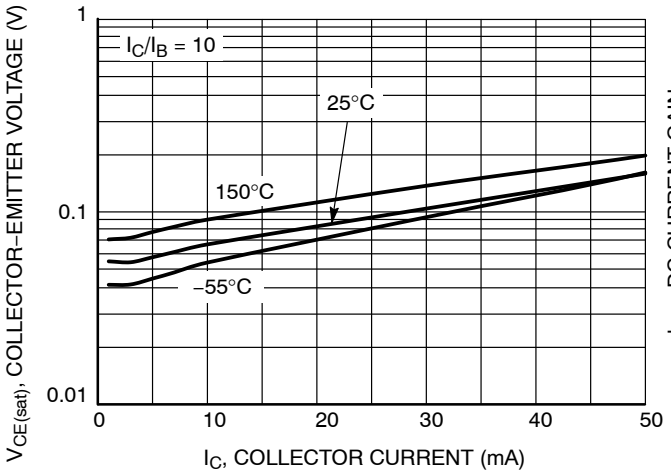


Figure 7. $V_{CE(sat)}$ vs. I_C

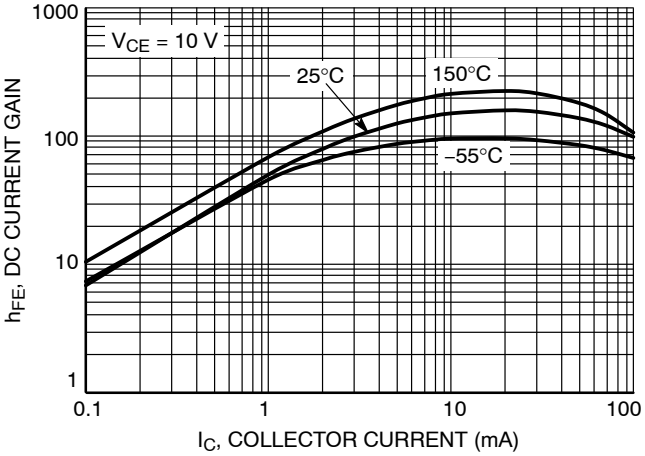


Figure 8. DC Current Gain

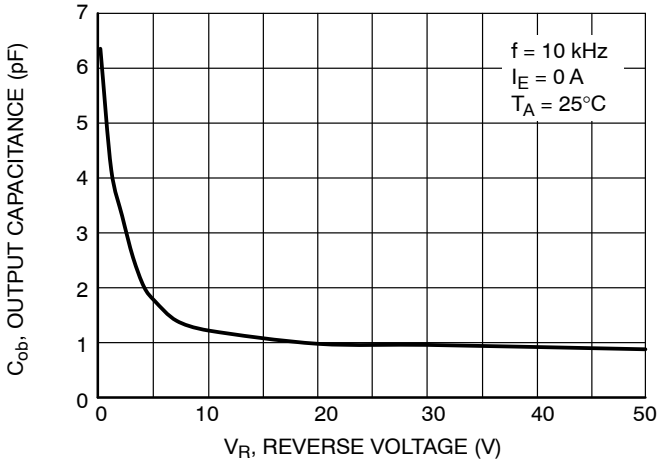


Figure 9. Output Capacitance

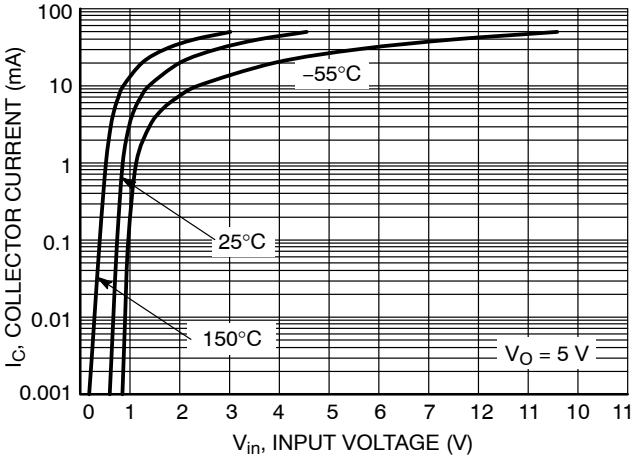


Figure 10. Output Current vs. Input Voltage

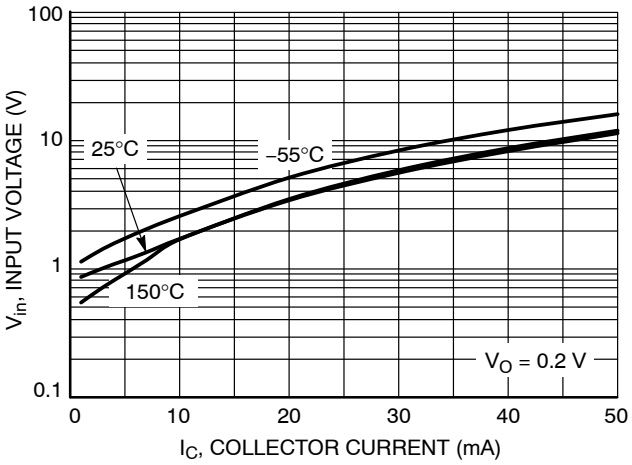
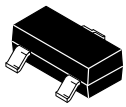


Figure 11. Input Voltage vs. Output Current

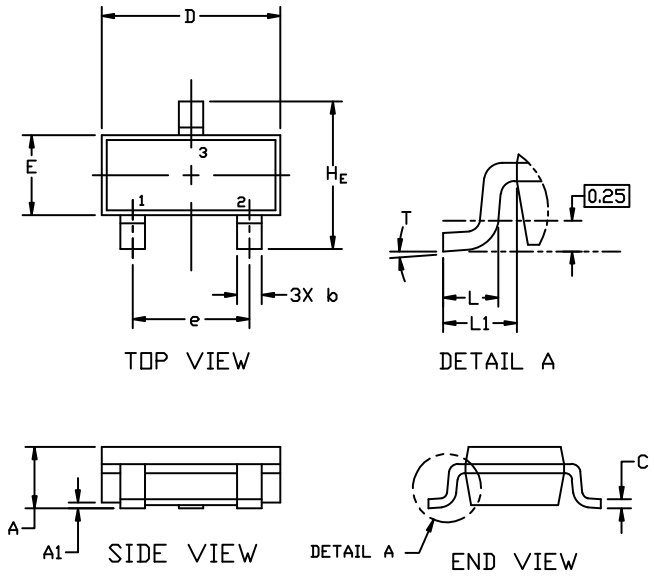
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

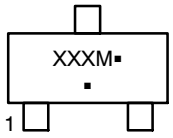


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

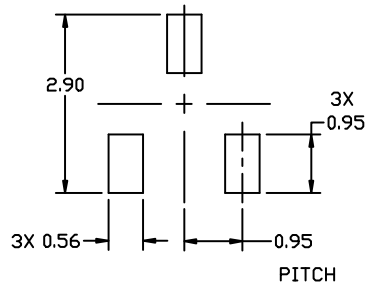
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

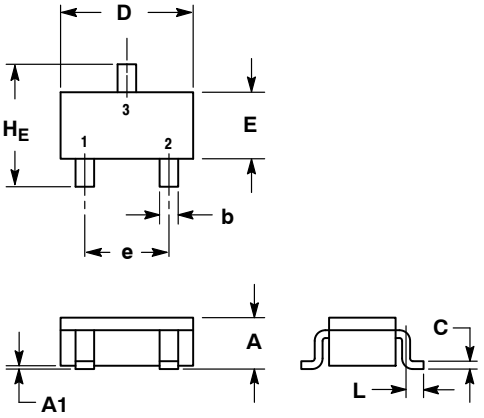
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

SCALE 2:1

SC−59
CASE 318D−04
ISSUE H

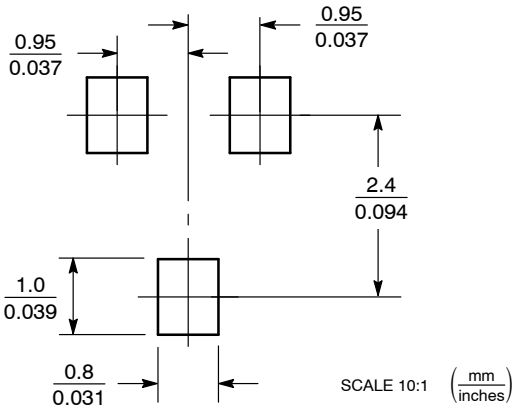
DATE 28 JUN 2012



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

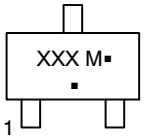
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.80	3.00	0.099	0.110	0.118

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

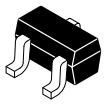
STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

DOCUMENT NUMBER:	**98ASB42664B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−59**	**PAGE 1 OF 1**

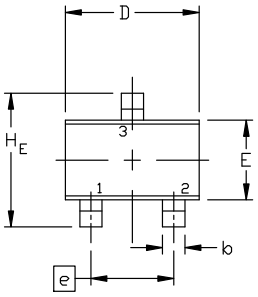
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



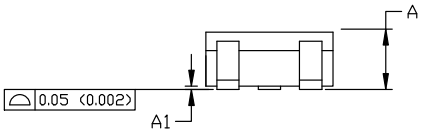
SCALE 4:1

SC−70 (SOT−323)
CASE 419
ISSUE R

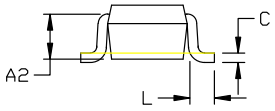
DATE 11 OCT 2022



TOP VIEW



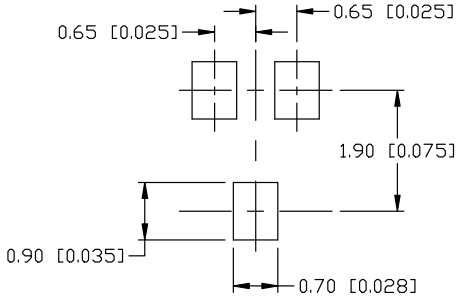
SIDE VIEW



END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

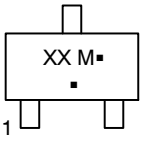
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

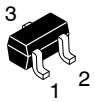
STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

DOCUMENT NUMBER:	**98ASB42819B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−70 (SOT−323)**	**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

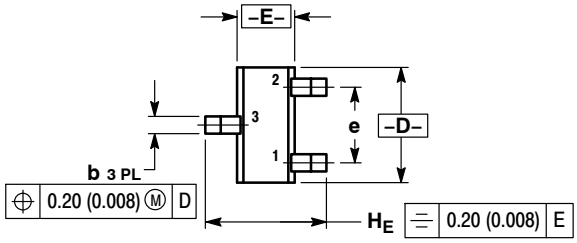
ON Semiconductor®

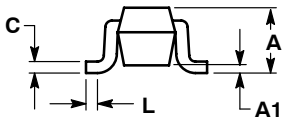


SCALE 4:1

SC−75/SOT−416
CASE 463−01
ISSUE G

DATE 07 AUG 2015





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H_E	1.50	1.60	1.70	0.060	0.063	0.067

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

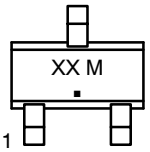
STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

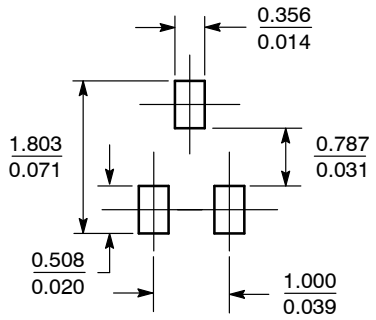
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

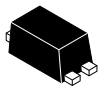
DOCUMENT NUMBER:	**98ASB15184C**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−75/SOT−416**	**PAGE 1 OF 1**

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

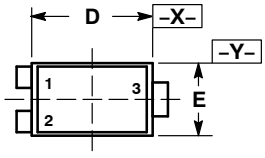
ON Semiconductor®

SOT−1123
CASE 524AA
ISSUE C

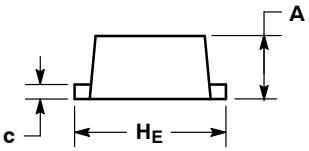
DATE 29 NOV 2011



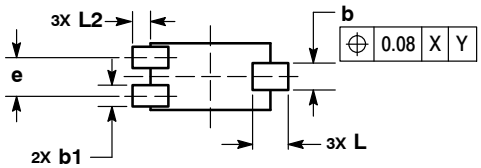
SCALE 8:1



TOP VIEW



SIDE VIEW

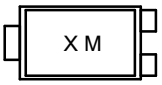


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
H_E	0.95	1.05
L	0.185 REF	
L2	0.05	0.15

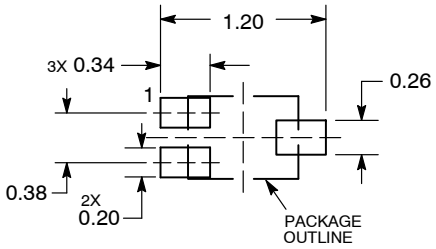
GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	**98AON23134D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−1123, 3−LEAD, 1.0X0.6X0.37, 0.35P**		**PAGE 1 OF 1**

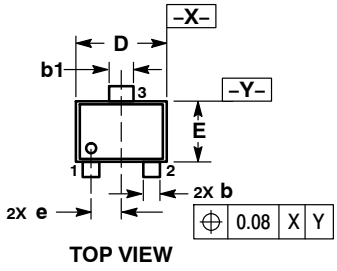
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

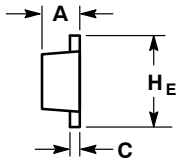
SOT−723
CASE 631AA−01
ISSUE D

DATE 10 AUG 2009

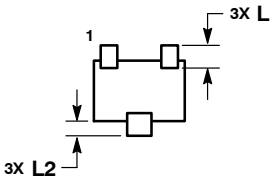
SCALE 4:1



TOP VIEW



SIDE VIEW



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

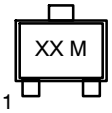
STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

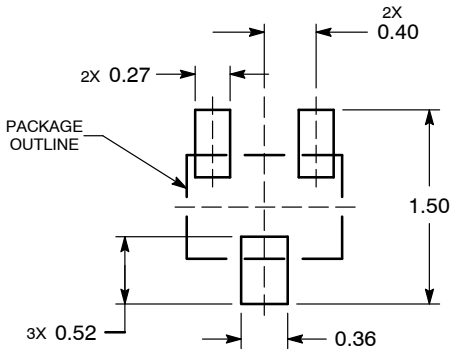
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G”, may or not be present.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON12989D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SOT−723**	**PAGE 1 OF 1**

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